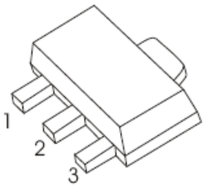
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89-3L Plastic-Encapsulate Transistors

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



KTA1273 TRANSISTOR (PNP)

FEATURES

- High Current
- Low Voltage
- Complementary to KTC3205

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-2	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V,I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-2V, I_C=-0.5A	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1.5A,I_B=-30mA			-2	V
Base-emitter voltage	V_{BE}	V_{CE}=-2V, I_C=-500mA			-1	V
Transition frequency	f_T	V_{CE}=-2V,I_C=-500mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		48		pF

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	100－200	160－320
MARKING	**1273**	

A,Nov,2010